

Figure S1. XPS core level scan of (a) C 1s, (b) O 1s, (c) Pt 4f and (d) survey scan taken on the Pt growth surface for the MeCpPtMe₃/O₂ process at 300°C, after the MeCpPtMe₃ pulse (1) and after the O₂ pulse (2).

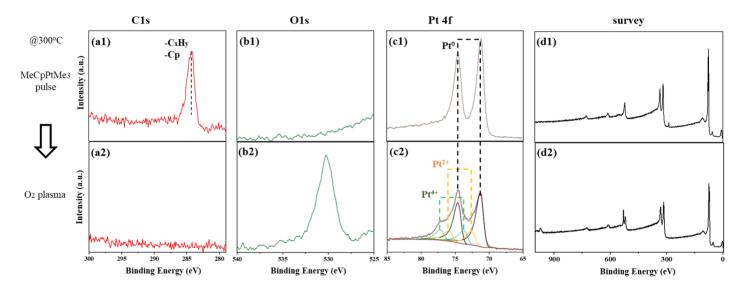


Figure S2. XPS core level scan of (a) C 1s, (b) O 1s, (c) Pt 4f and (d) survey scan taken on the Pt growth surface for the MeCpPtMe₃/O₂* process at 300°C, after the MeCpPtMe₃ pulse (1) and after O₂* pulse (2).

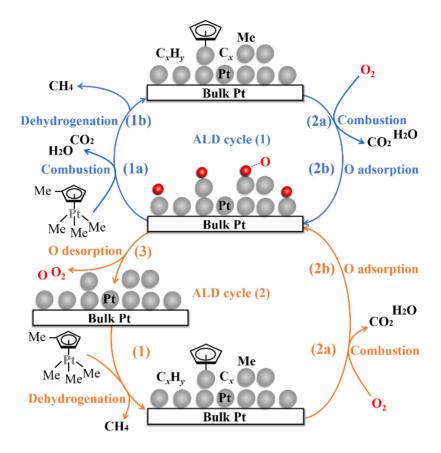


Figure S3. Growth mechanisms proposed for the MeCpPtMe₃/O₂ process. ALD cycle (1) and (2) indicate the standard process and the 3-step process with 50 min. waiting after O₂ step to remove surface O species.

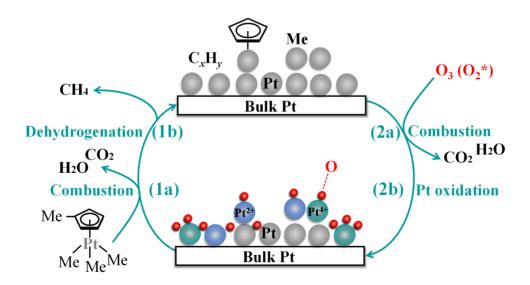


Figure S4. Growth mechanisms proposed for the MeCpPtMe₃ and O₃(O₂*) based process.